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DOT MATRIX LED DISPLAY(2.0Inch)



Lead-Free Parts

LMD5721/2AEGR-XX/P2-PF

DATA SHEET

DOC. NO : QW0905-LMD5721/2AEGR-XX/P2-PF

REV. : A

DATE : 16 - Feb - 2009





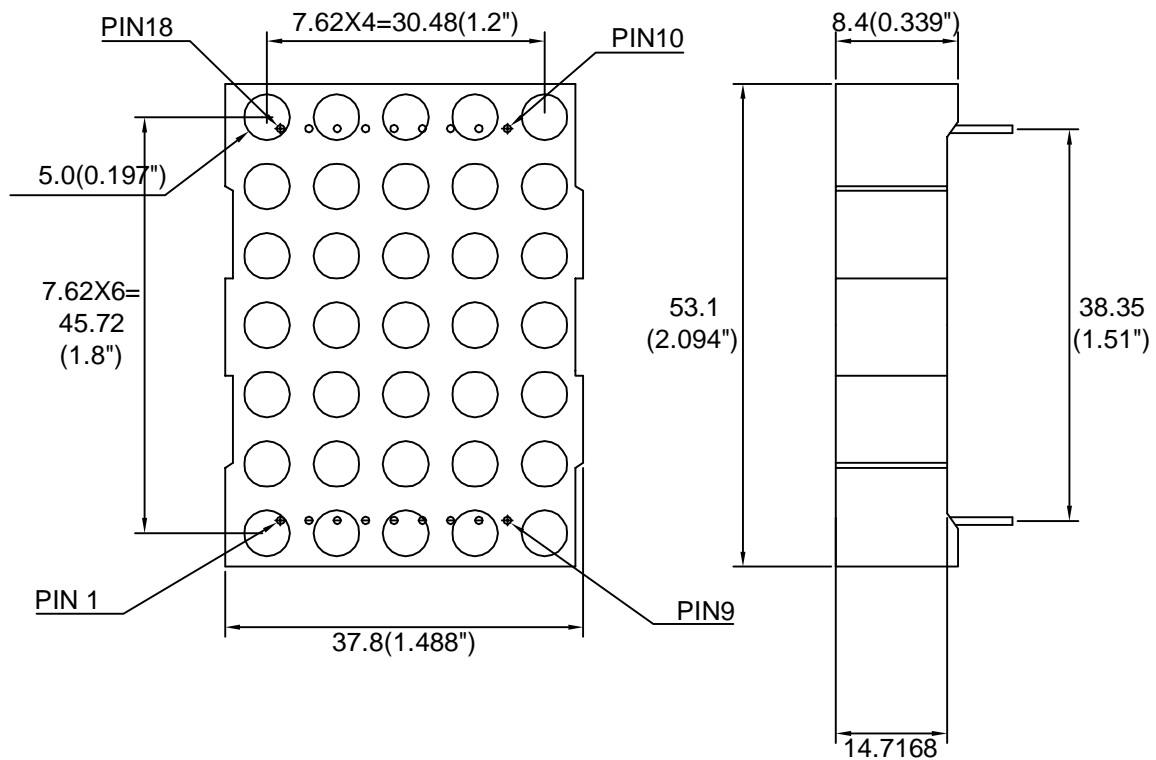
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PART NO. LMD5721/2AEGR-XX/P2-PF

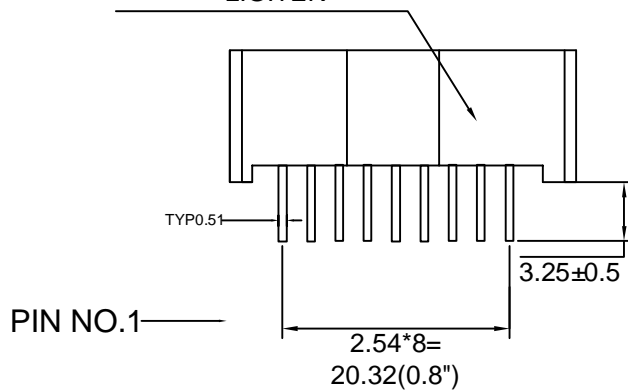
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Package Dimensions



LMD5721/2AEGR-XX/P2-PF

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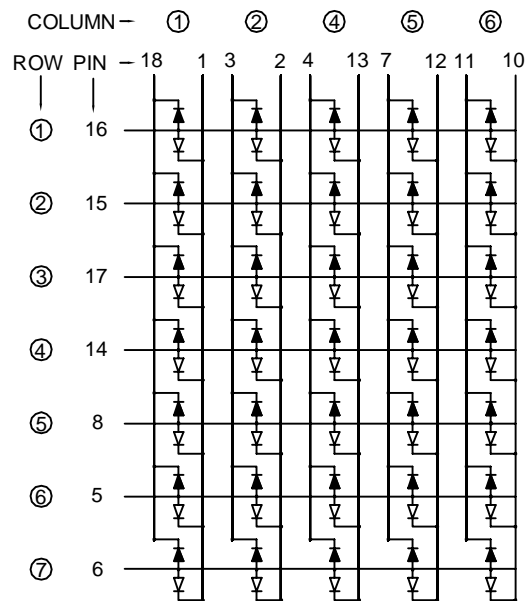


Note : 1.All dimension are in millimeters and (Inch) tolerance is ± 0.25 mm unless otherwise noted.
2.Specifications are subject to change without notice.

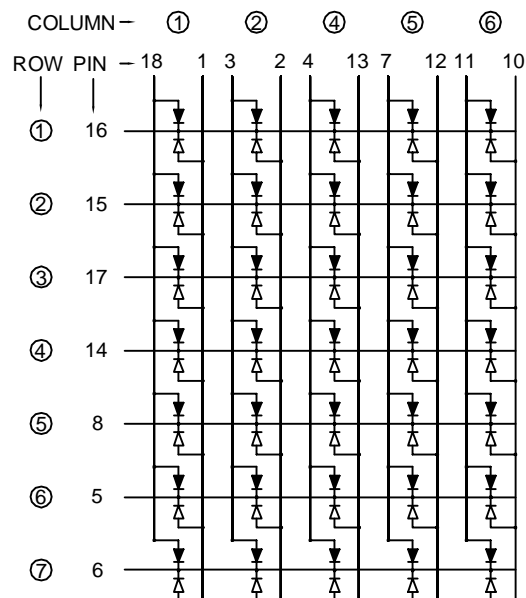


Internal Circuit Diagram

LMD5721AEGR-XX/P2-PF



LMD5722AEGR-XX/P2-PF





Electrical Connection

PIN NO.	LMD5721AEGR-XX/P2-PF	PIN NO.	LMD5722AEGR-XX/P2-PF
1	Cathode Column 1 (Green)	1	Anode Column 1 (Green)
2	Cathode Column 2 (Green)	2	Anode Column 2 (Green)
3	Cathode Column 2 (Red)	3	Anode Column 2 (Red)
4	Cathode Column 3 (Red)	4	Anode Column 3 (Red)
5	Anode Row 6	5	Cathode Row 6
6	Anode Row 7	6	Cathode Row 7
7	Cathode Column 4 (Red)	7	Anode Column 4 (Red)
8	Anode Row 5	8	Cathode Row 5
9	No Connect	9	No Connect
10	Cathode Column 5 (Green)	10	Anode Column 5 (Green)
11	Cathode Column 5 (Red)	11	Anode Column 5 (Red)
12	Cathode Column 4 (Green)	12	Anode Column 4 (Green)
13	Cathode Column 3 (Green)	13	Anode Column 3 (Green)
14	Anode Row 4	14	Cathode Row 4
15	Anode Row 2	15	Cathode Row 2
16	Anode Row 1	16	Cathode Row 1
17	Anode Row 3	17	Anode Row 3
18	Cathode Column 1 (Red)	18	Anode Column 1 (Red)



Absolute Maximum Ratings at Ta=25

Parameter	Symbol	Ratings		UNIT
		E	G	
Forward Current Per Chip	IF	30	30	mA
Peak Forward Current Per Chip (Duty 1/10,0.1ms Pulse Width)	IFP	120	120	mA
Power Dissipation Per Chip	PD	100	100	mW
Reverse Current Per Any Chip	Ir	10		μ A
Operating Temperature	Topr	-25 ~ +85		
Storage Temperature	Tstg	-25 ~ +85		

Part Selection And Application Information(Ratings at 25)

PART NO	CHIP		common cathode or anode	P (nm)	(nm)	Electrical					IV-M
	Material	Emitted				Vf(v)			Iv(mcd)		
						Min.	Typ.	Max.	Min.	Typ.	
LMD5721AEGR-XX/P2-PF	GaAsP/GaP	Orange	Common Cathode	640	45	1.7	2.1	2.6	4.0	7.2	2:1
	GaP	Green		565	30	1.7	2.1	2.6	5.0	8.5	
LMD5722AEGR-XX/P2-PF	GaAsP/GaP	Orange	Common Anode	640	45	1.7	2.1	2.6	4.0	7.2	
	GaP	Green		565	30	1.7	2.1	2.6	5.0	8.5	

Note : 1.The forward voltage data did not including ±0.1V testing tolerance.
2. The luminous intensity data did not including ±15% testing tolerance.



Test Condition For Each Parameter

Parameter	Symbol	Unit	Test Condition
Forward Voltage Per Chip	Vf	volt	If=20mA
Luminous Intensity Per Chip	Iv	mcd	If=10mA
Peak Emission Wavelength	P	nm	If=20mA
Spectral Line Half-Width		nm	If=20mA
Reverse Current Any Chip	Ir	μ A	Vr=5V
Luminous Intensity Matching Ratio	IV-M		



Typical Electro-Optical Characteristics Curve

E CHIP

Fig.1 Forward current vs. Forward Voltage

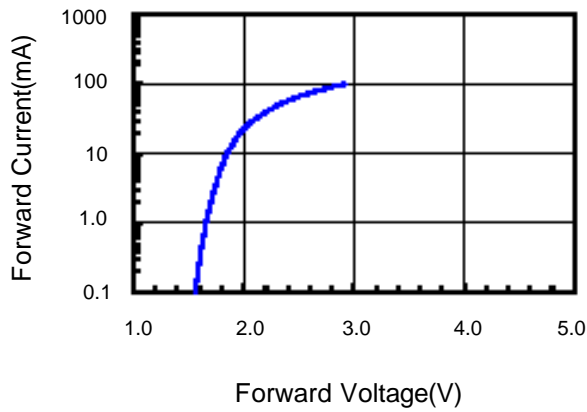


Fig.2 Relative Intensity vs. Forward Current

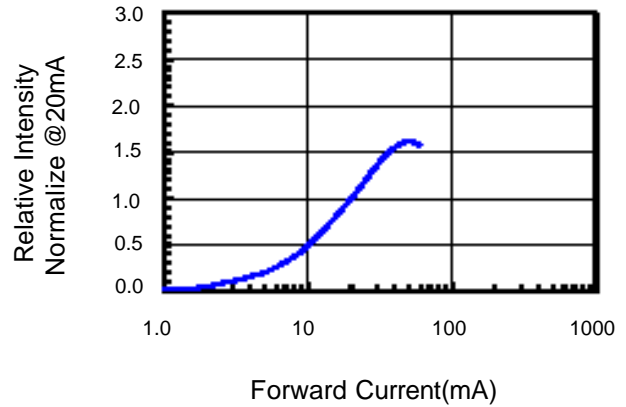


Fig.3 Forward Voltage vs. Temperature

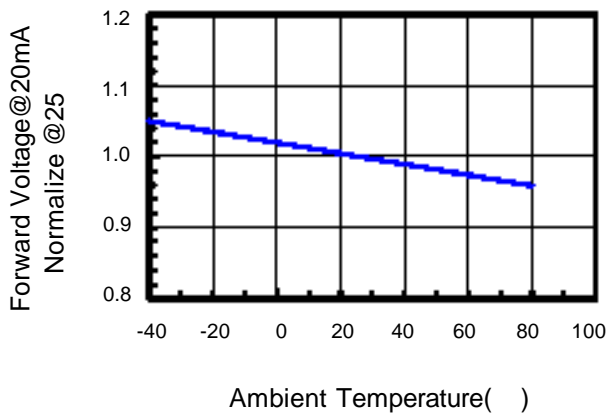


Fig.4 Relative Intensity vs. Temperature

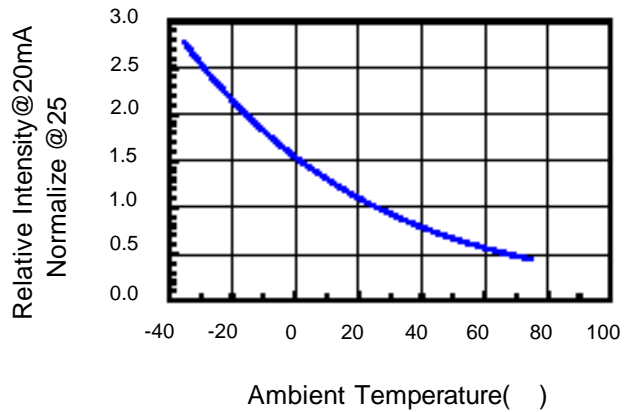
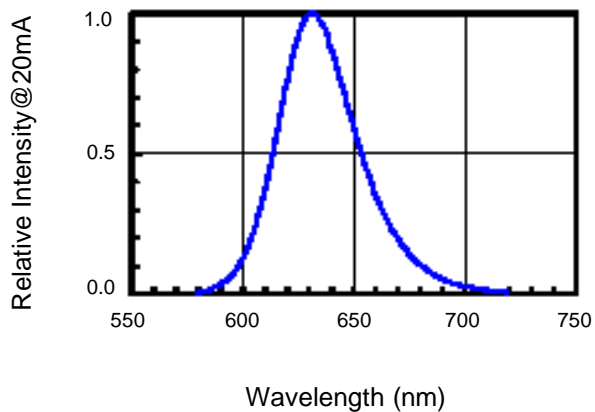


Fig.5 Relative Intensity vs. Wavelength





Typical Electro-Optical Characteristics Curve

G CHIP

Fig.1 Forward current vs. Forward Voltage

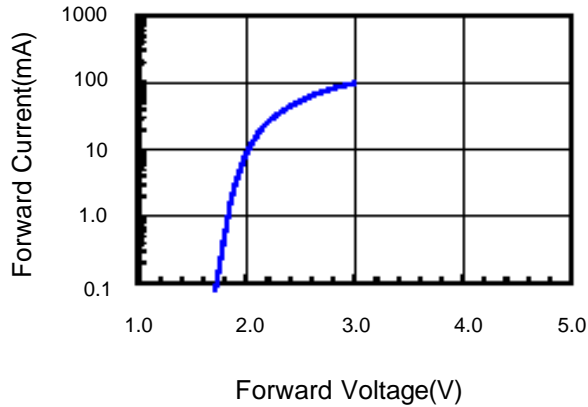


Fig.2 Relative Intensity vs. Forward Current

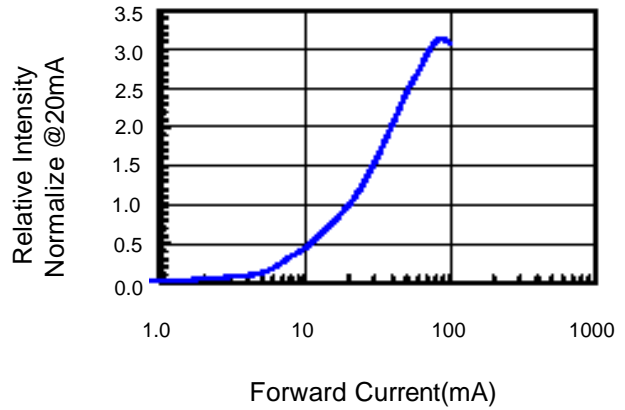


Fig.3 Forward Voltage vs. Temperature

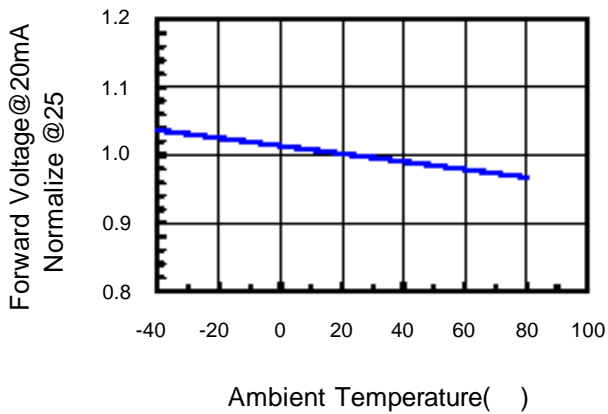


Fig.4 Relative Intensity vs. Temperature

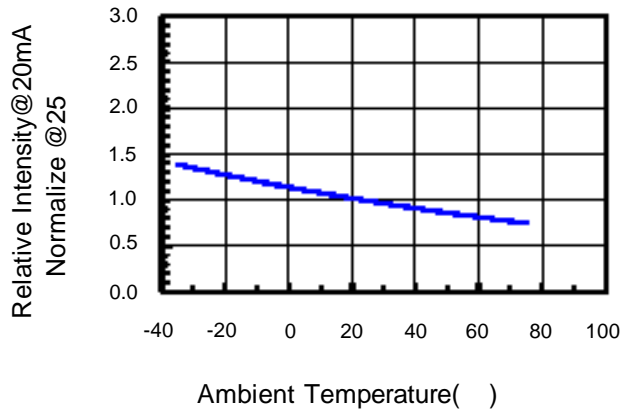
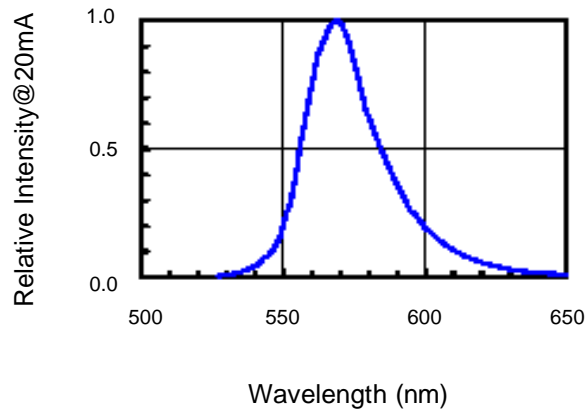


Fig.5 Relative Intensity vs. Wavelength





Soldering Condition(Pb-Free)

1.Iron:

Soldering Iron:30W Max

Temperature 350 ° C Max

Soldering Time:3 Seconds Max(One time only)

Distance:Solder Temperature 1/16 Inch Below Seating
Plane For 3 Seconds At 260 ° C

2.Wave Soldering Profile

Dip Soldering

Preheat: 120° C Max

Preheat time: 60seconds Max

Ramp-up

2° C/sec(max)

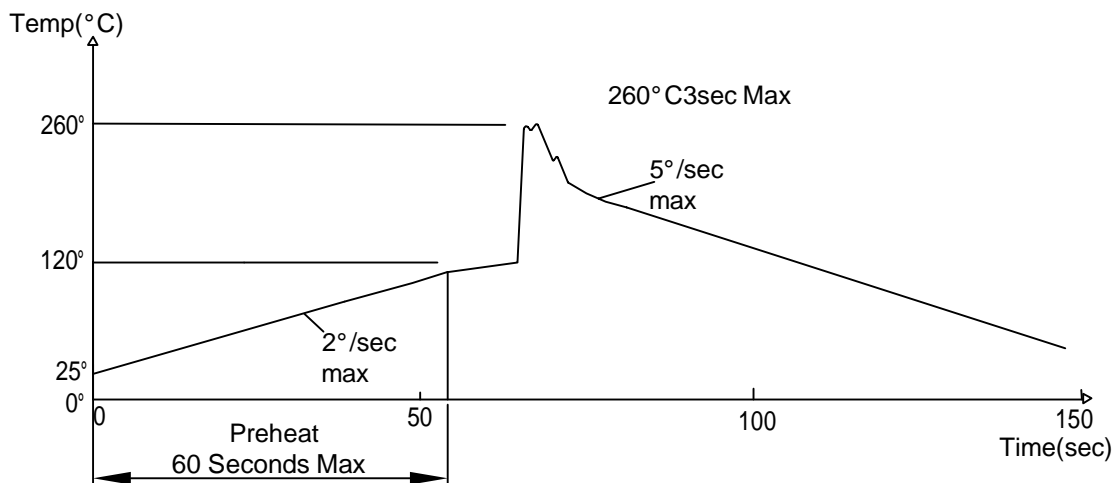
Ramp-Down:-5° C/sec(max)

Solder Bath:260° C Max

Dipping Time:3 seconds Max

Distance:Solder Temperature 1/16 Inch Below Seating

Plane For 3 Seconds At 260° C



Note: 1.Wave solder should not be made more than one time.
2.You can just only select one of the soldering conditions as above.



Reliability Test:

Test Item	Test Condition	Description	Reference Standard
Operating Life Test	1.Under Room Temperature 2.If=10mA 3.t=1000 hrs (-24hrs, +72hrs)	This test is conducted for the purpose of determining the resistance of a part in electrical and thermal stressed.	MIL-STD-750: 1026 MIL-STD-883: 1005 JIS C 7021: B-1
High Temperature Storage Test	1.Ta=105 ±5 2.t=1000 hrs (-24hrs, +72hrs)	The purpose of this is the resistance of the device which is laid under condition of high temperature for hours.	MIL-STD-883:1008 JIS C 7021: B-10
Low Temperature Storage Test	1.Ta=-40 ±5 2.t=1000 hrs (-24hrs, +72hrs)	The purpose of this is the resistance of the device which is laid under condition of low temperature for hours.	JIS C 7021: B-12
High Temperature High Humidity Test	1.Ta=65 ±5 2.RH=90%~95% 3.t=240hrs ±2hrs	The purpose of this test is the resistance of the device under tropical for hours.	MIL-STD-202:103B JIS C 7021: B-11
Thermal Shock Test	1.Ta=105 ±5 & -40 ±5 (10min) (10min) 2.total 10 cycles	The purpose of this is the resistance of the device to sudden extreme changes in high and low temperature.	MIL-STD-202: 107D MIL-STD-750: 1051 MIL-STD-883: 1011
Solder Resistance Test	1.T.Sol=260 ±5 2.Dwell time= 10 ±1sec.	This test intended to determine the thermal characteristic resistance of the device to sudden exposures at extreme changes in temperature when soldering the lead wire.	MIL-STD-202: 210A MIL-STD-750: 2031 JIS C 7021: A-1
Solderability Test	1.T.Sol=230 ±5 2.Dwell time=5 ±1sec	This test intended to see soldering well performed or not.	MIL-STD-202: 208D MIL-STD-750: 2026 MIL-STD-883: 2003 JIS C 7021: A-2